

ABSTRACT:

A method of manufacturing a magnetic tunnel junction device, in which a stack (1) comprising two electrode layers (3, 7) and a barrier layer (5) extending in between is formed. One of the electrode layers is structured by means of etching, in which, during etching, a part of this layer is made thinner by removing material until a rest layer (7r) remains. This rest layer is subsequently removed by means of physical etching, in which at least substantially charged particles have a motion energy which is between the sputtering threshold of the magnetic material of the rest layer and the sputtering threshold of the non-magnetic material of the barrier layer. In the relevant method, it is prevented that the electrode layer which is not to be structured is detrimentally influenced during structuring of the other electrode layer.

Fig. 1E

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